

T-aSi (Oxidation&doped Si)

Designed to form an integrated Oxidation and doped Si passivation on the rear side of solar cell to improve its efficiency.

SOLAR TECHNOLOGY CELL PROCESS MACHINE

Technical Specification

Format(mm)	5,140(W) x 8,950(L) x 4,200(H)
Weight(kg)	10,600 * 2
Gas Supply	SiH4, H2, PH3, B2H6, O2
Number of Chamber	10
Cycle Time(min)	48
Uptime(%)	94
Boat Capacity	468 wafers/Boat
Wafer Throughput	5,800 wafers with boat wafer 468
Cell Type	Monocrystalline, Multicrystalline Silicon wafers
Cell Size(mm)	M2(156*156) ~ M6(166*166)
Cell Thickness(um)	120 ~ 200(±20)
Process Temperature(°C)	200 ~ 550
Process Pressure(Torr)	0.5 ~ 3.0

Dimension

